SARDAR PATEL UNIVERSITY

M.Sc. (Physics)(IIIrd Semester) Examination

Date: 24/10/2018, Day: Wednesday, Time: 2:00 p.m. to 5:00 p.m. Subject: Nanoscience and Thin film Physics, Paper No. PS03CPHY22

CBCS(choice based credit system)

Important Note: Q.1: Multiple choice questions (MCQ) carries one mark each.

Q.2: Short questions carries two marks each (attempt any seven out of nine)

70

| | Qio to | Q.o : Long questions carrie | s 12 marks . | | |
|-----|---|--|---|--|--|
| | | | | Total Marks: | |
| Q.1 | Choose the | appropriate options from | the following in Q.1 | (8) | |
| 1 | Objective lens in (a) Second | TEM produces the(b) third | image of the object | ? (d) fourth | |
| 2 | Thin films is an (a) 3D | example of which type of (b) 1D | of nanostructure (c) 2D | (d) 0D | |
| 3 | For III-V and II- energy gap is no (a) red shift | -VI semiconductors the to gative which means that (b) blue shift | emperature coefficient the absorption undergo (c) green shift | (dE _g /dT) of the es (d) yellow shift | |
| 4 | Who derived the (a)Raoult | eoretical model for sputte (b) Clausius-Clap | ring phenomena ? eyron (c) Sig | mund (d) Hertz | |
| 5 | In infrared detect the below quanti (a) electric curre | ors, the responsivity of the ty generated per watt of it ent (b) temperate | ncoming radiation. | in terms of which of (d) pressure | |
| 6 | Source vapor source sur (a)Surface | | ngle between vapor dir Point and surface | ection and normal (d) Cylindrical | |
| 7 | Which of the following optical method is used to measure the thickness of Opaque film | | | | |
| | (a)FET | (b) Stylus-Profilometr | y (c) VAMFO | (d) Ellipsometry | |
| 8 | gas is used for reactive evaporation and reactive sputtering techniques for thin film deposition. | | | | |
| | (a) Oxygen | (b) Nitrogen | (c)Methane | (d) All of these | |
| | | | | P.T.O. | |

| Q.2 | Answer any seven questions out of nine in Q.2 | |
|----------|--|------------|
| 1 | For a conducting sample which microscope is useful to study its surface at atomic level. Differentiate between its different at the study its surface at | (14) |
| | atomic level. Differentiate between its different modes. | t |
| 2 | How dark field image and bright field image is obtained in Troy to | |
| 3 | - ************************************ | |
| 4 | Obtain vapors pressure of the elements value of | |
| 5 | Obtain vapors pressure of the elements using Clausius -Clapeyron equation. Why Ion plating method is known as hybrid method? Explain Ion plating method in brief. | · |
| 6 | Explain Ion-surface interaction. | |
| 7 | State how nanomaterials can be useful for high definition TV and flat-panel displays. | |
| 8 | How Brillouin spectroscopy differs from Raman Spectroscopy. | |
| 9 | List out the mechanical techniques for film thickness measurement. Explain Crystal Oscillator method in brief. | |
| Q.3(a) | Describe Reverse micelles and solved | |
| Q.3(b) | Explain how quantum dots can be formed using photolithography technique. | (6) (6) |
| Q.3(b) | Discuss dynamic light scattering(DLS) method used for estimating the size of nanoparticles. | (6) |
| Q.4(a) | For the passage of electrons one by one than 1 THE | |
| | For the passage of electrons one by one through FET-type nanostructure, explain how single electron tunneling takes place in this type of device. | (6) |
| Q.4(b) | Explain Raman spectroscopy with suitable diagrams for studying nanomaterials. | (6) |
| Q.4(b) | By taking suitable examples, explain how infrared surface spectroscopy can be helpful to study nanomaterials. | (6) |
| Q.5(a) | Define evaporation Rate. What is the difference between evaporation of compound and alloys? Explain Raoult's law for evaporation of alloys and its limitations. | (6) |
| Q.5(b) | Discuss in detail electron beam method with different types of electron beam guns. | (6) |
| Q.5(b) | OR | |
| Q13(D) - | Define sputtering and sputtering yield? Discuss various sputtering regimes: (a) Single knock on (b) Linear collision cascade | (6) |
| Q.6(a) | Write a detail note on chemical vapour deposition and different reactions involved. | (6) |
| Q.6(b) | Describe Ionized cluster beam deposition method. Write down advantages and disadvantage of this method. | (6) |
| Q.6(b) | Write the working principle of optical method for film thickness measurement and describe optical thickness measurements method for transparent film. | (6) |

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